

# Innovations in DDR Memory Simulation

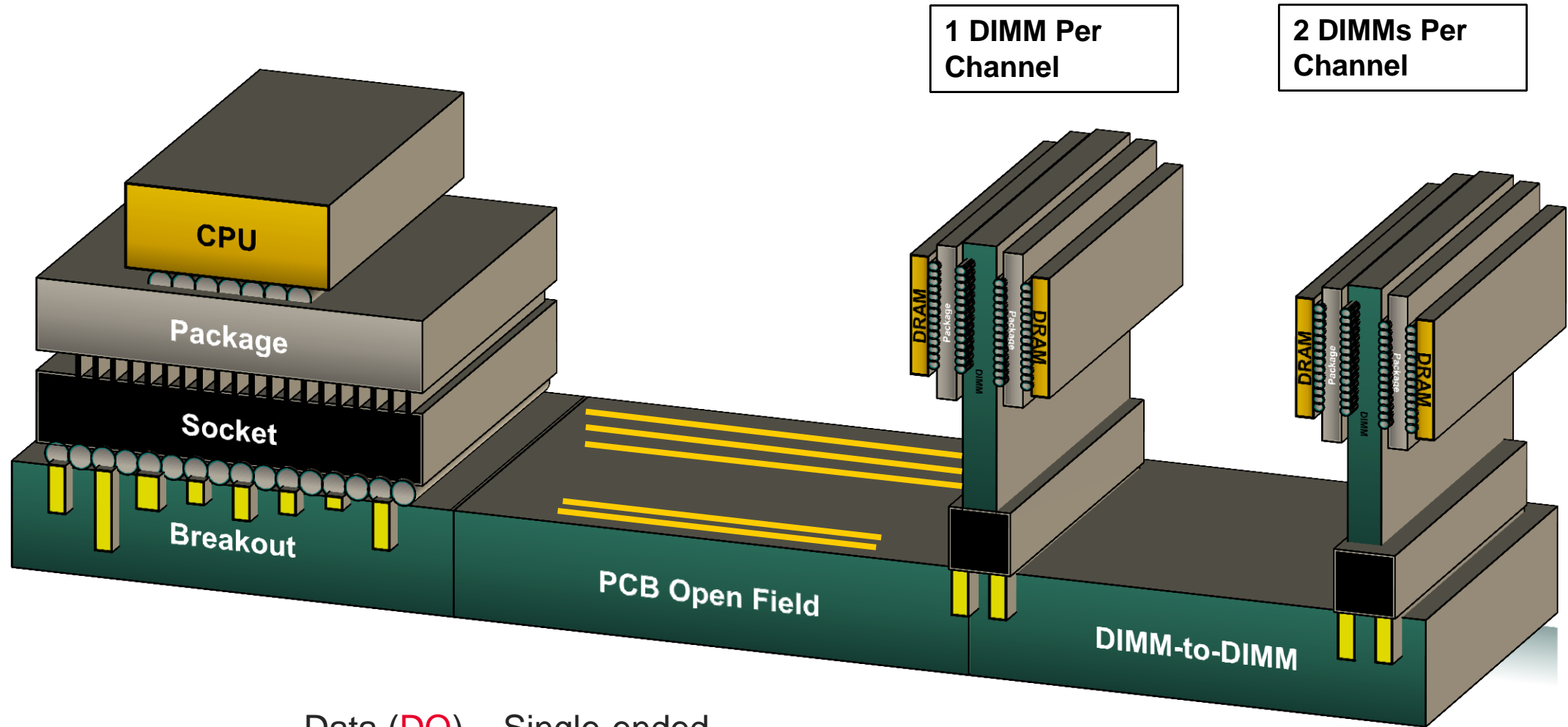
*Stephen Slater*

**NOVEMBER 1, 2019**

*Asian IBIS Summit, Shanghai, PRC*



# A Typical DDR5 Application



Data (DQ) – Single-ended  
Data Strobe (DQS) – Differential  
Microstrip & Stripline

# What Does it Mean to Succeed?

THE MEASURE OF SUCCESS FOR A PRODUCT WITH DDR5

- No system failures, under stress
  - At Max and Min temperatures
  - Using multiple vendors' DIMMs
  - 1 DIMM slot and 2 DIMM slots filled
  - Running diagnostic software that stresses the memory access
  - Graceful performance degradation

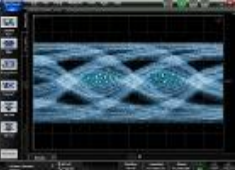

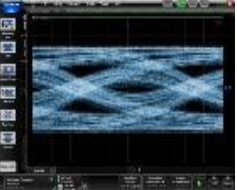
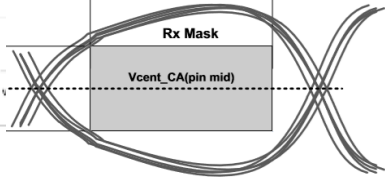
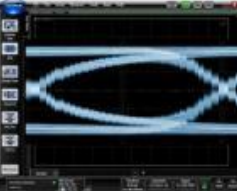
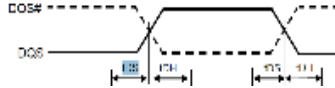
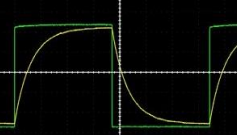
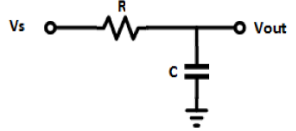
“I can stop testing when I’m certain my manager is satisfied with the **product quality risk**”



Source: Burn-in environment test chambers by EDA-Industries S.p.a

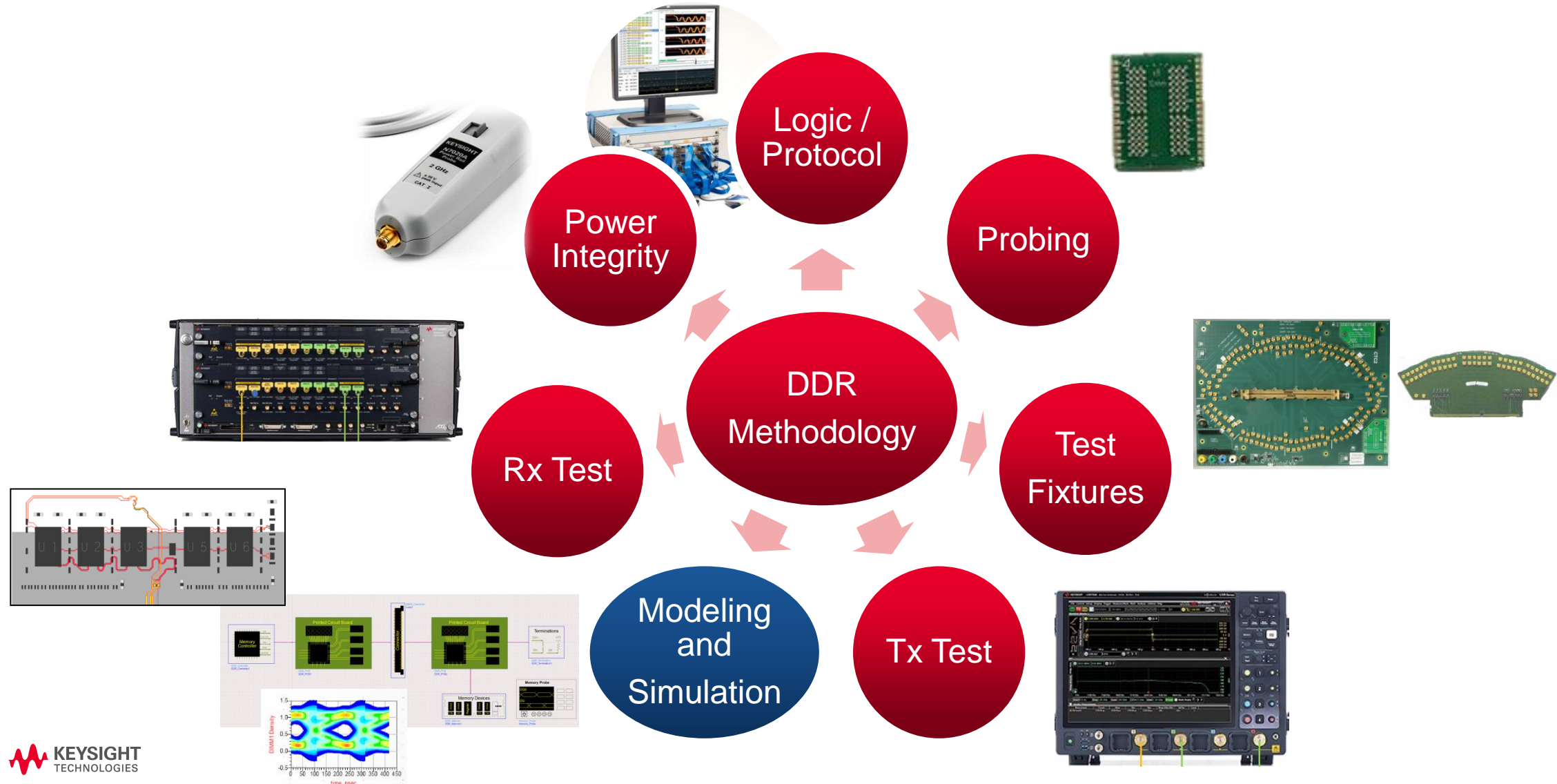
# How Did we Get to DDR5?

## A ROAD PAVED BY INNOVATION

Signal	MT/s	Generation	Characteristics	Specification	Introduction
	4200 – 8000+	DDR5+	<p><b>“Hyper Speed”</b></p> <ul style="list-style-type: none"> <li>• Eye collapses</li> <li>• Impulse response</li> <li>• BER Rj/Dj, Rn/Dn</li> </ul>		2019
	1600 – 4200	DDR4	<p><b>“Serial Speed”</b></p> <ul style="list-style-type: none"> <li>• Eye Diagrams</li> <li>• Rx Masks</li> <li>• Bit error rates</li> </ul>		2014
	200 – 1600	DDR/2/3	<p><b>“High Speed Digital”</b></p> <ul style="list-style-type: none"> <li>• Transmission lines</li> <li>• Ts / Th, Skew</li> </ul>		2002
	33 – 133	SDRAM	<p><b>“Low Speed”</b></p> <ul style="list-style-type: none"> <li>• Fanout</li> <li>• Capacitance</li> </ul>		1961

# Ensuring First Pass Success - One Layer Deeper

ENSURING THE SYSTEM IS PERFORMANT AND RELIABLE



# Change, Challenges and Solutions

1. Crosstalk, Jitter and Bit-Error-Rate (BER) Specs
2. Closed eyes need equalization and training
3. Innovations in Simulation and Modeling of DDR5 & LPDDR5 systems

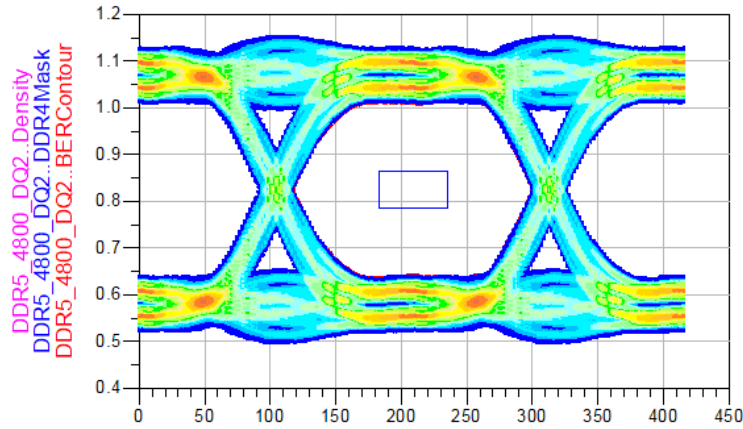


# 1. Crosstalk, Jitter and Bit-Error-Rate (BER) Specs

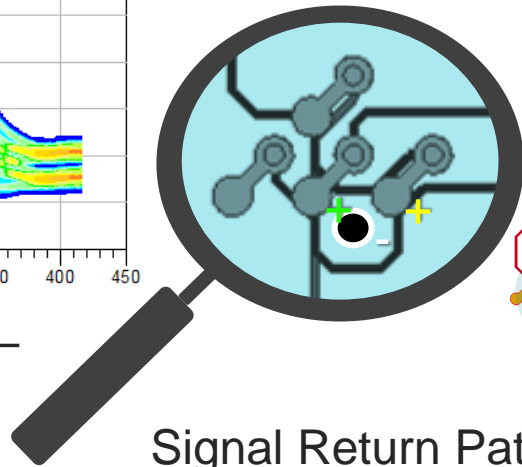
# Crosstalk

## THE IMPORTANCE OF THE SIGNAL RETURN PATH

DDR5-4800

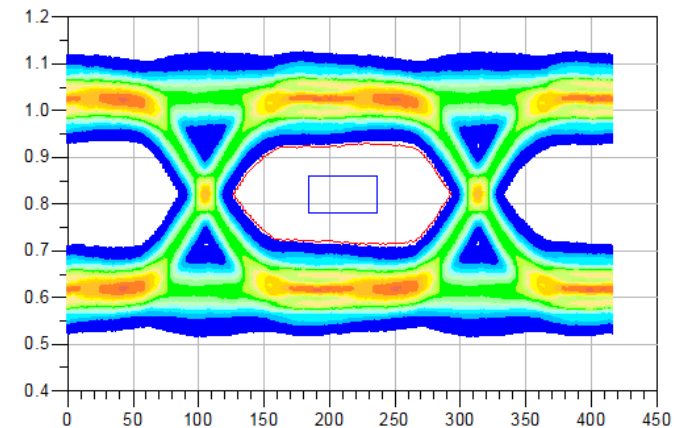
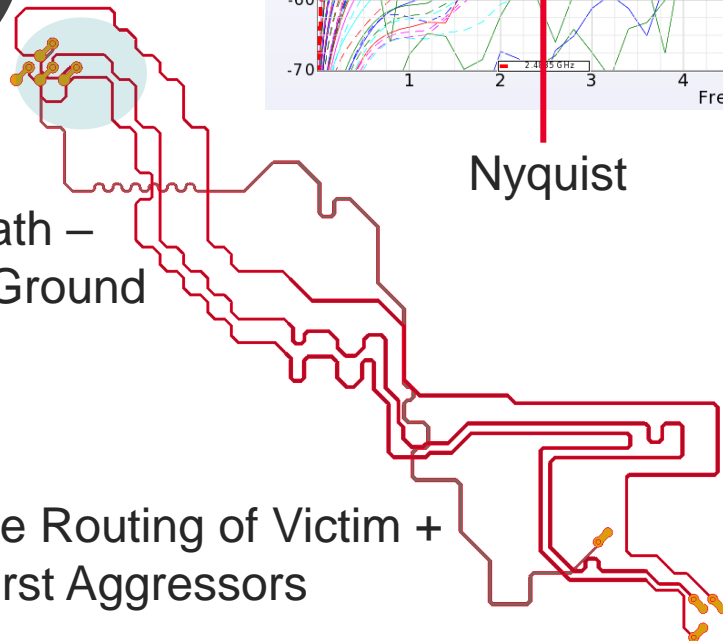
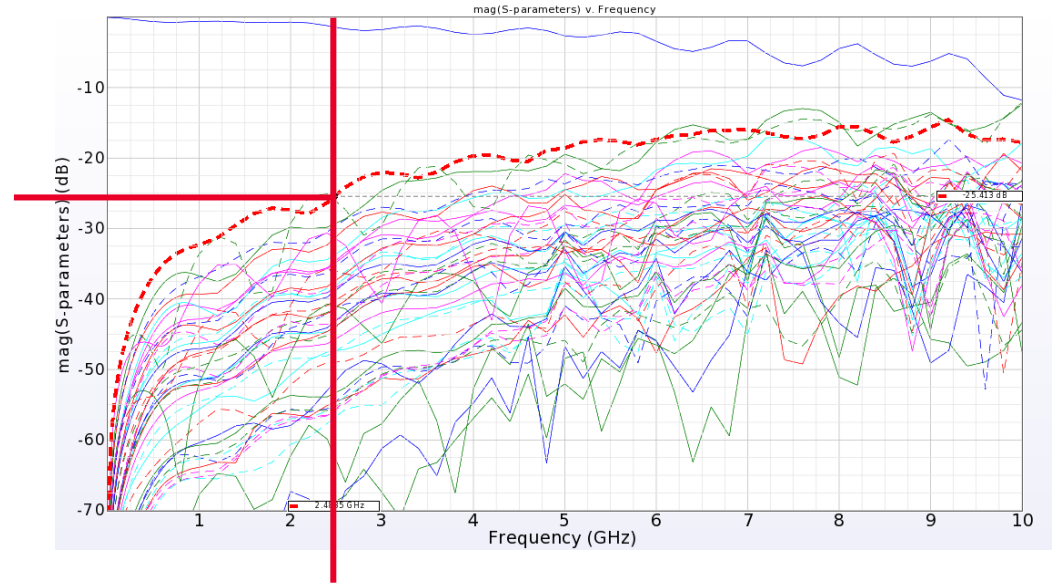


No Crosstalk, No Jitter –  
Just ISI from Channel



Signal Return Path –  
through shared Ground  
Pin

< -25dB



With Crosstalk

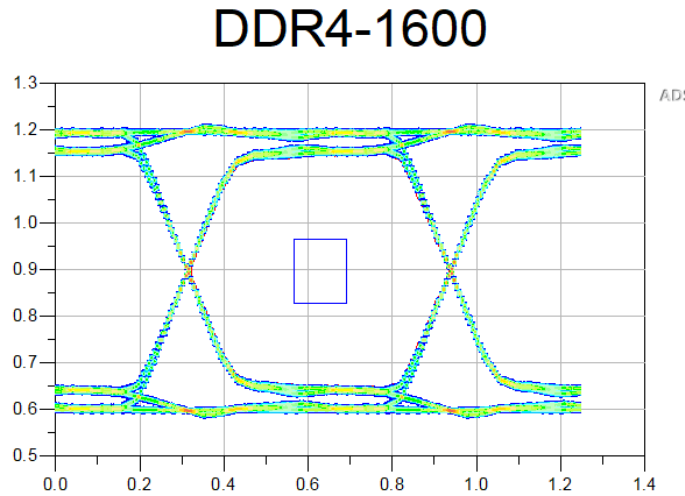


# Jitter

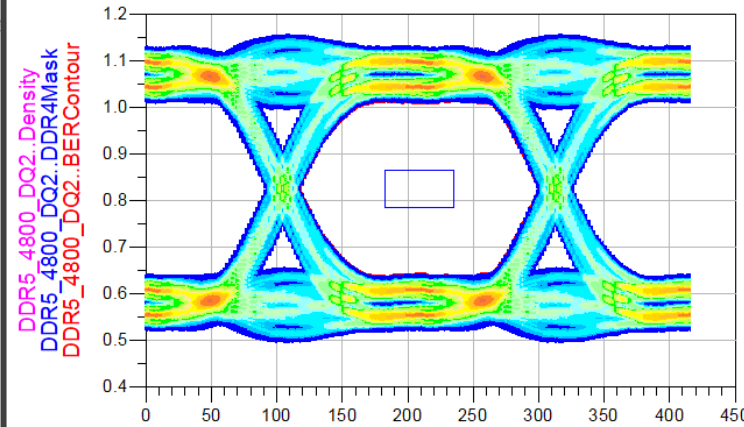
Jitter injected at Tx, and eye measured at the DRAM Solder-Ball (Rx Input)

BER CONTOUR AT 1E-16 TELLS US THE REAL MARGIN

No Jitter –  
Just ISI from  
Channel



DDR5-4800

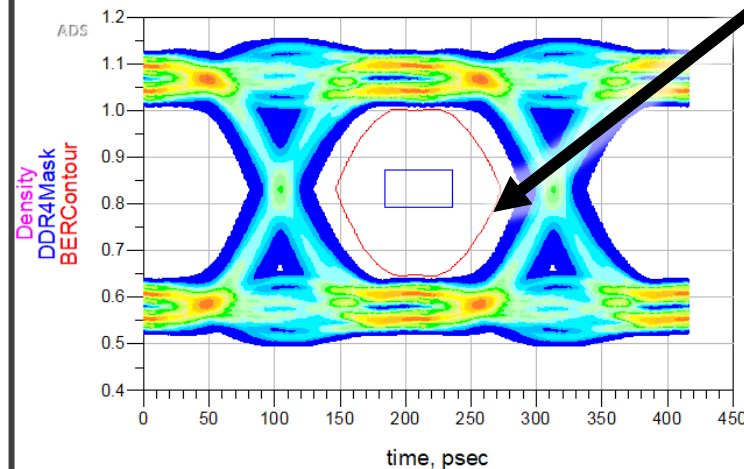
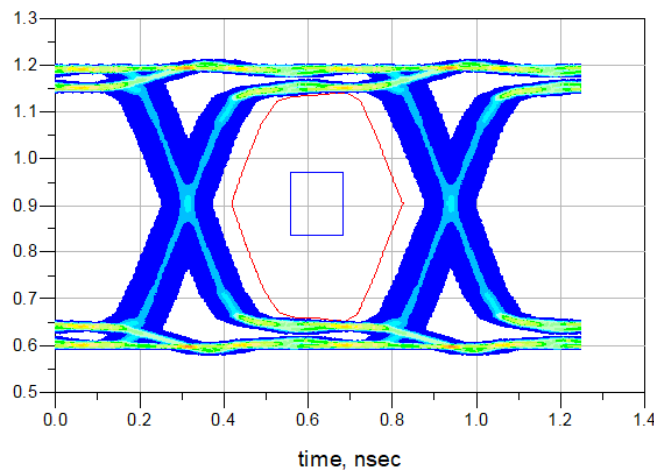


No Jitter –  
More ISI from  
Channel due to  
higher speed

47% Reduction in  
Timing Margin

(27ps less margin to  
mask)

Random Jitter  
= 0.02 UI  
Applied at Tx  
(2%)



# Specs Becoming More Bit-Error-Rate Focused

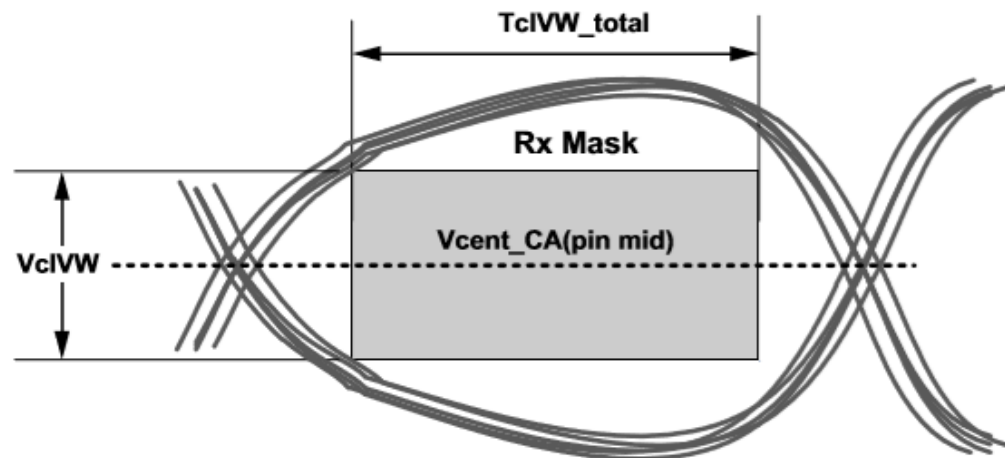


Figure 179 — CA Receiver (Rx) mask

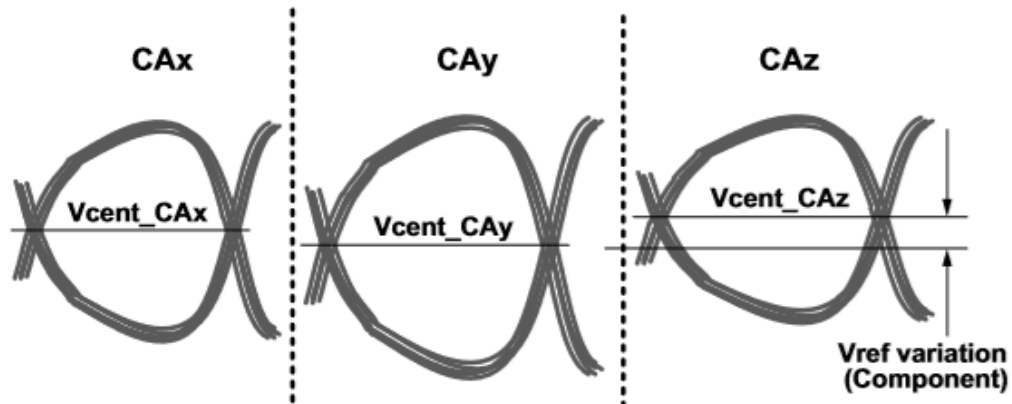


Figure 180 — Across pin  $V_{REFCA}$  voltage variation

- From the draft spec:
  - Maximum Jitter ( $D_j$ ,  $R_j$  and DCD) specifications for Tx and Rx components
  - For Tx and Rx Voltage and Timing tests, system BER is  $e^{-16}$  and requires **5.3e9 minimum UIs** for validation (99.5% confidence level)
  - New receiver stressed-eye tests for components and DIMMs

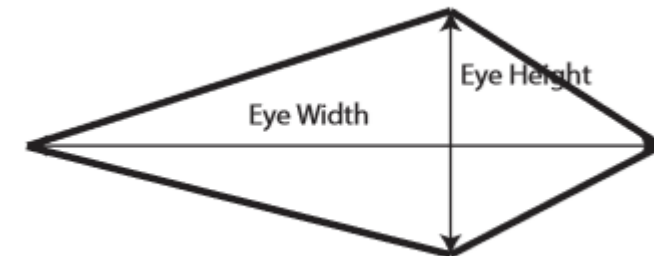


Figure 196 — Example of Rx Stressed Eye Height and Eye Width

Stressed Eye is calibrated to a specified height and width. The DIMM, DRAM or Memory Controller Rx must be able to receive to the system BER

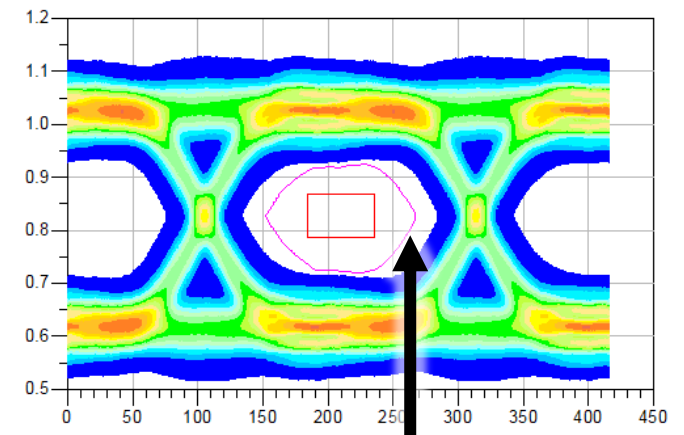
# Crosstalk, Jitter & BER Specs

## KEY INSIGHTS

- Jitter and Crosstalk are Very Significant
- Simulation must predict Eye closure due to Random Jitter down to the system BER ( $1e-16$ ) in a practical time
- EM simulation must capture Crosstalk accurately

### DDR5-4800

Jitter, crosstalk & Channel ISI



64% Reduction in  
Voltage Margin

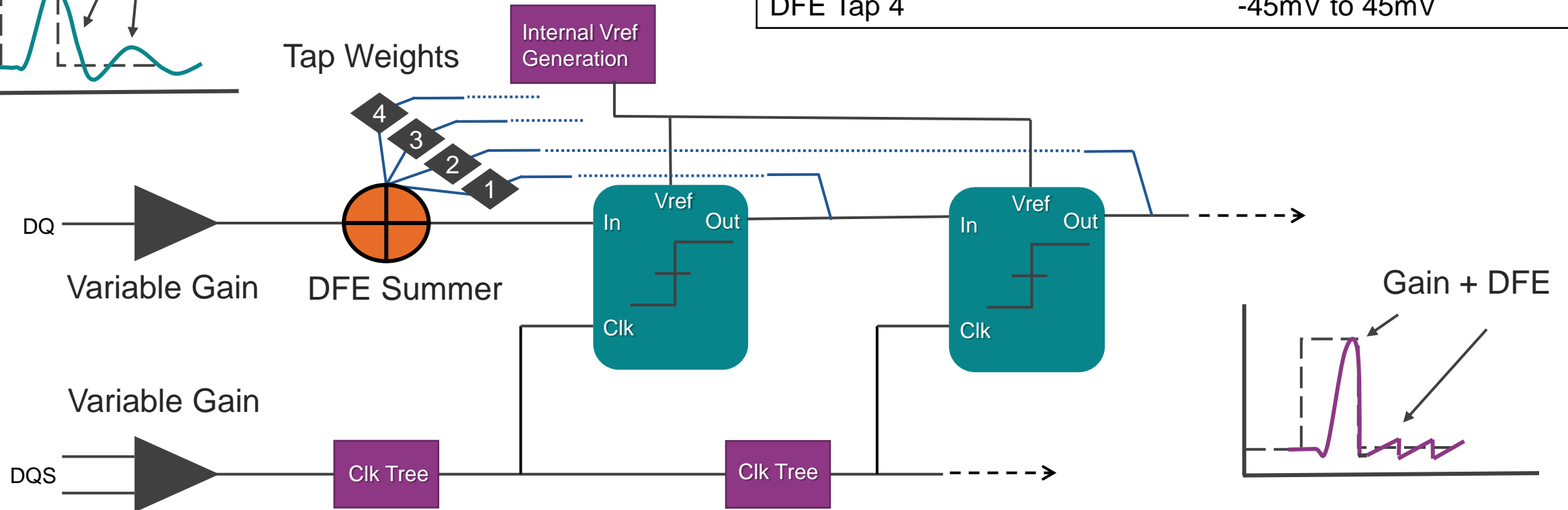
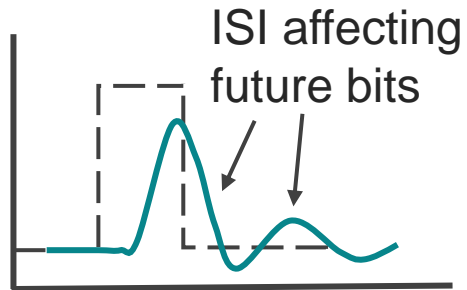
63% Reduction in  
Timing Margin



## 2. Equalization and Training

# Rx Equalization

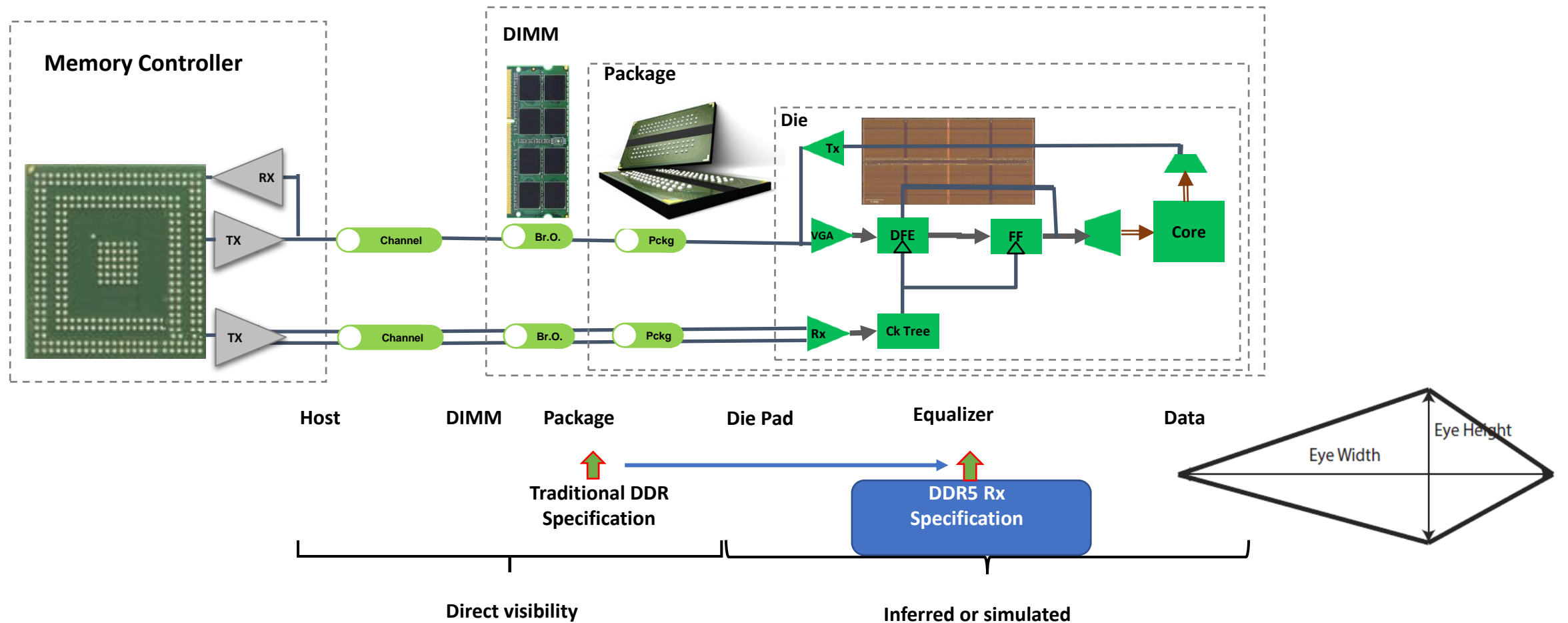
**FIRST TIME TO HAVE DFE ON DRAM!**



## Mode Register Settings (per DQ) *All values subject to change*

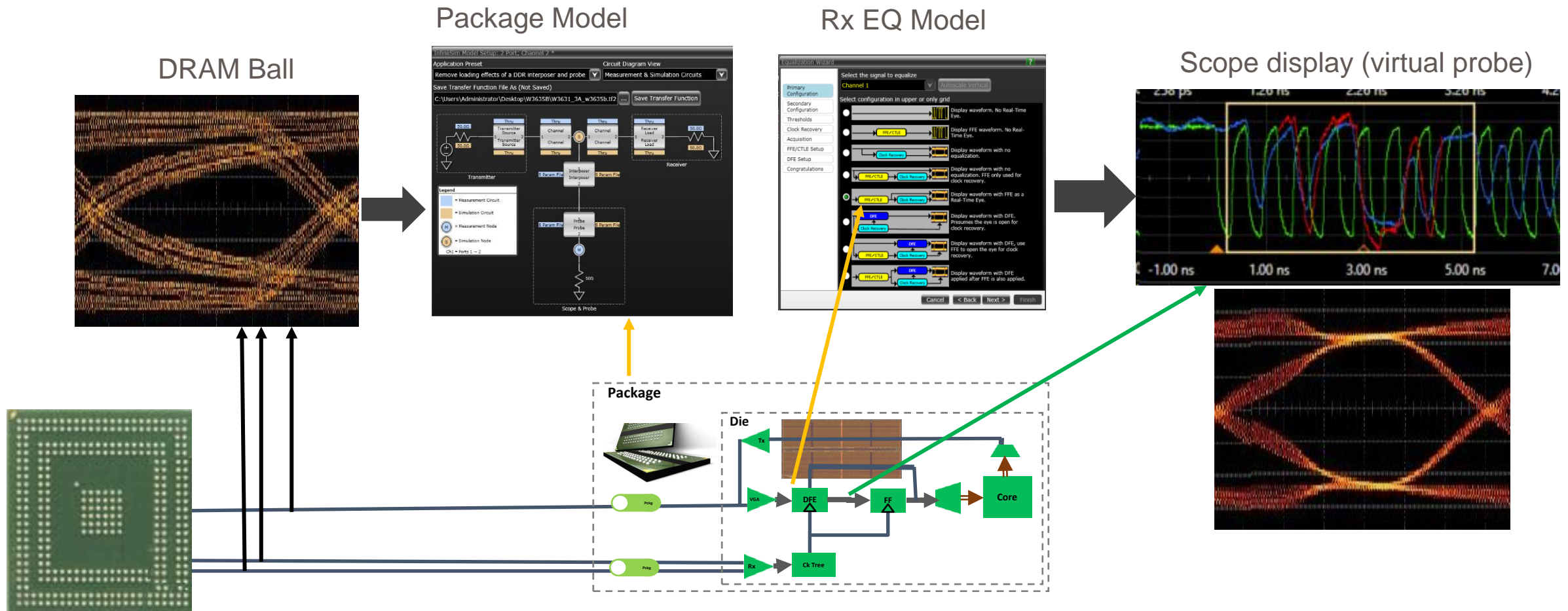
Variable Gain	-6dB to 6dB
VrefDQ	-3 to +3 Offset steps
DFE Tap 1	-200mV to 50mV
DFE Tap 2	-75mV to 75mV
DFE Tap 3	-60mV to 60mV
DFE Tap 4	-45mV to 45mV

# DDR5 Rx Specifications are Inside the Die



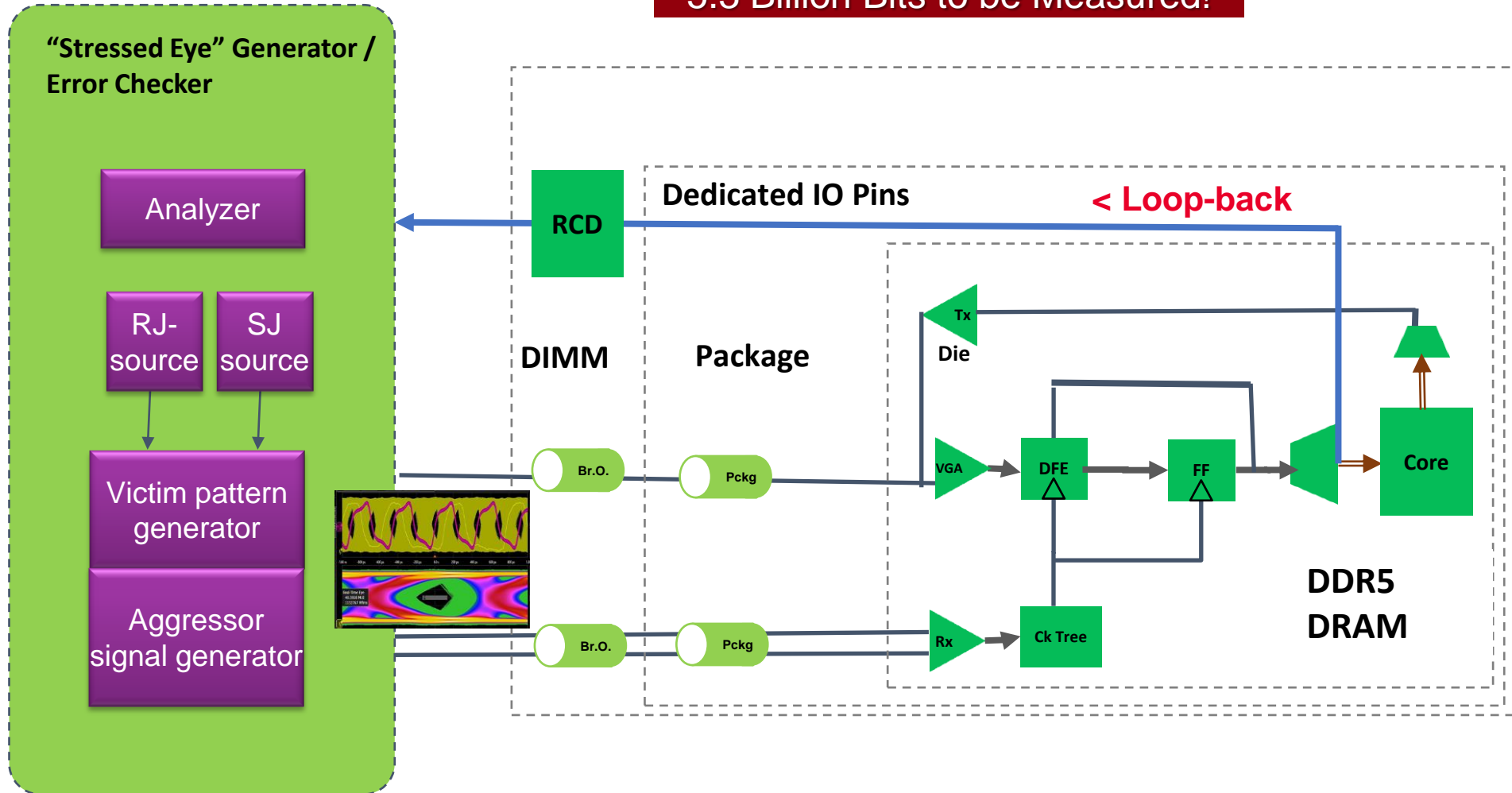
# DDR5 Tx Test: New Methodology Needed

VIRTUAL PROBING INSIDE THE DIE



# DDR5 Rx Test: New DRAM Feature - Loop-Back Mode

5.3 Billion Bits to be Measured!





# Skew Adjustment with Write-Leveling

- Due to the fly-by topology of the clock for DDR4 & DDR5, the Clock (Clk) is inevitably skewed to the DQS at each of the independent DRAM

This can be done in Simulation too!



- The controller has ability to adjust skew between DQ's, DQS and the Clock signal.
- DQS is adjusted to match the Clk first, then internal alignment of each DQ is performed (via mode register) to remove DQ-to-DQS skew (due to the package and die)

# Equalization and Training

## KEY INSIGHTS

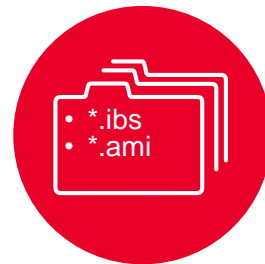
- Possible to have a Closed eye at input to Rx
- Optimal Eye opening depends on:
  - Vref setting (per DQ)
  - Gain Setting (per DQ)
  - DFE Tap settings (4 taps per DQ)
  - Timing of DQS to DQ
  - Write-leveling (skew adjustment)



### **3. Innovations in Simulation and Modeling of DDR5 & LPDDR5 systems**

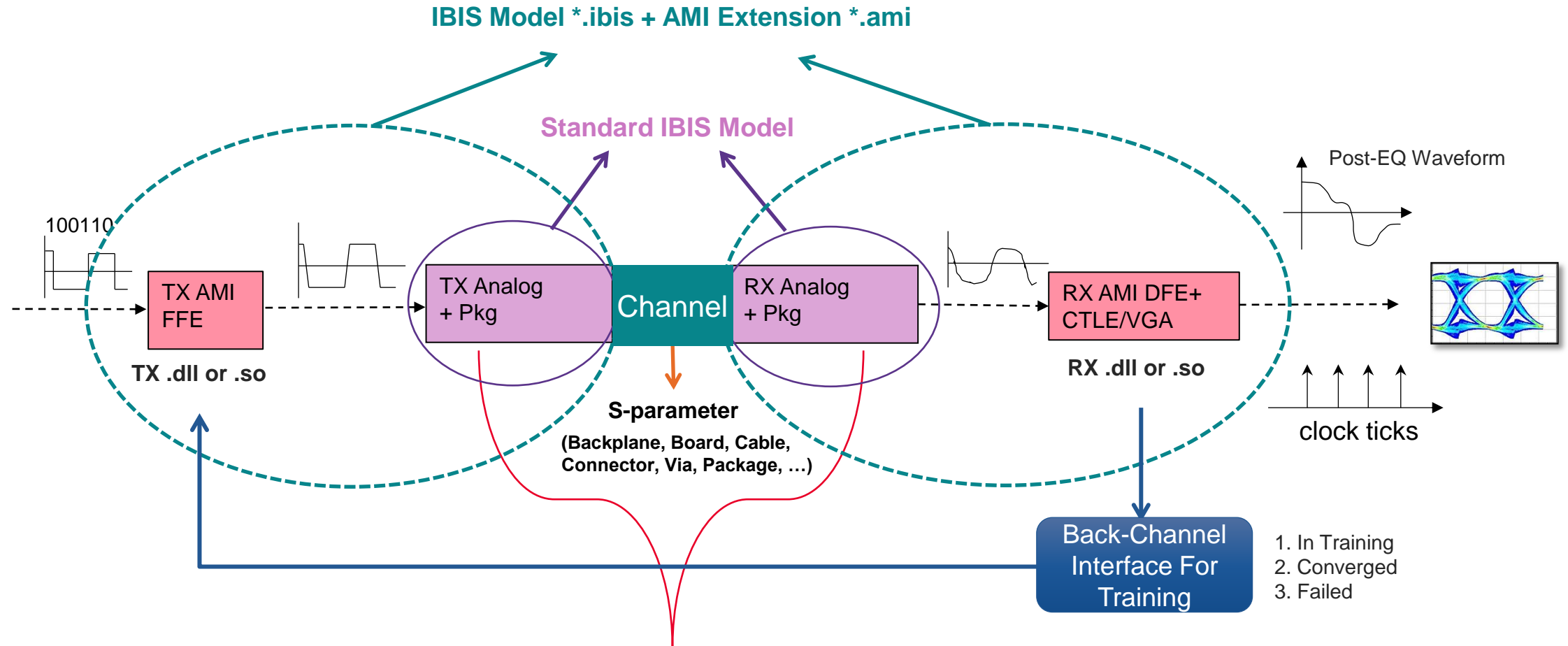
# Introducing IBIS AMI for DDR Signals

- EQ Necessary for TX: 3 Tap Pre-Emphasis (Feed Forward Equalization)
- EQ Necessary for RX: CTLE/VGA/DFE
- IBIS-AMI offers
  - Portability – One IBIS-AMI mode can run on many EDA tools
  - IP Protection – Digital signal processing behavior is concealed in model DLL/shared object
  - Interoperability - IC Vendor A ↔ IC Vendor B (AMI defines a common interface between the vendor model and the EDA channel simulator)
  - Non-linearity – As complex as the model vendor wishes the model to be
  - Performance – Ultra low BER simulations in seconds not days over the traditional SPICE simulation
- AMI has been widely adopted by IC, system and EDA companies for SerDes signals but this is the first application to DDR **single-ended** signals.



# How Does Standard IBIS-AMI Work?

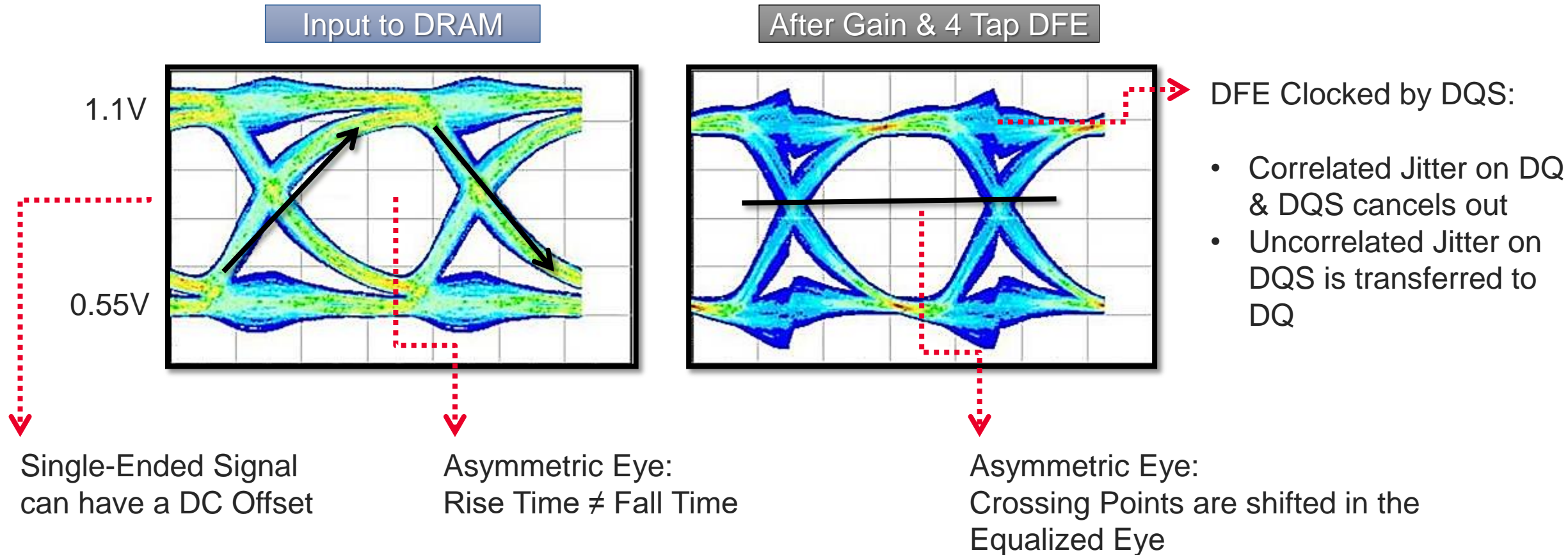
## CHANNEL SIMULATION



Impulse response of a Linear Time Invariant Network

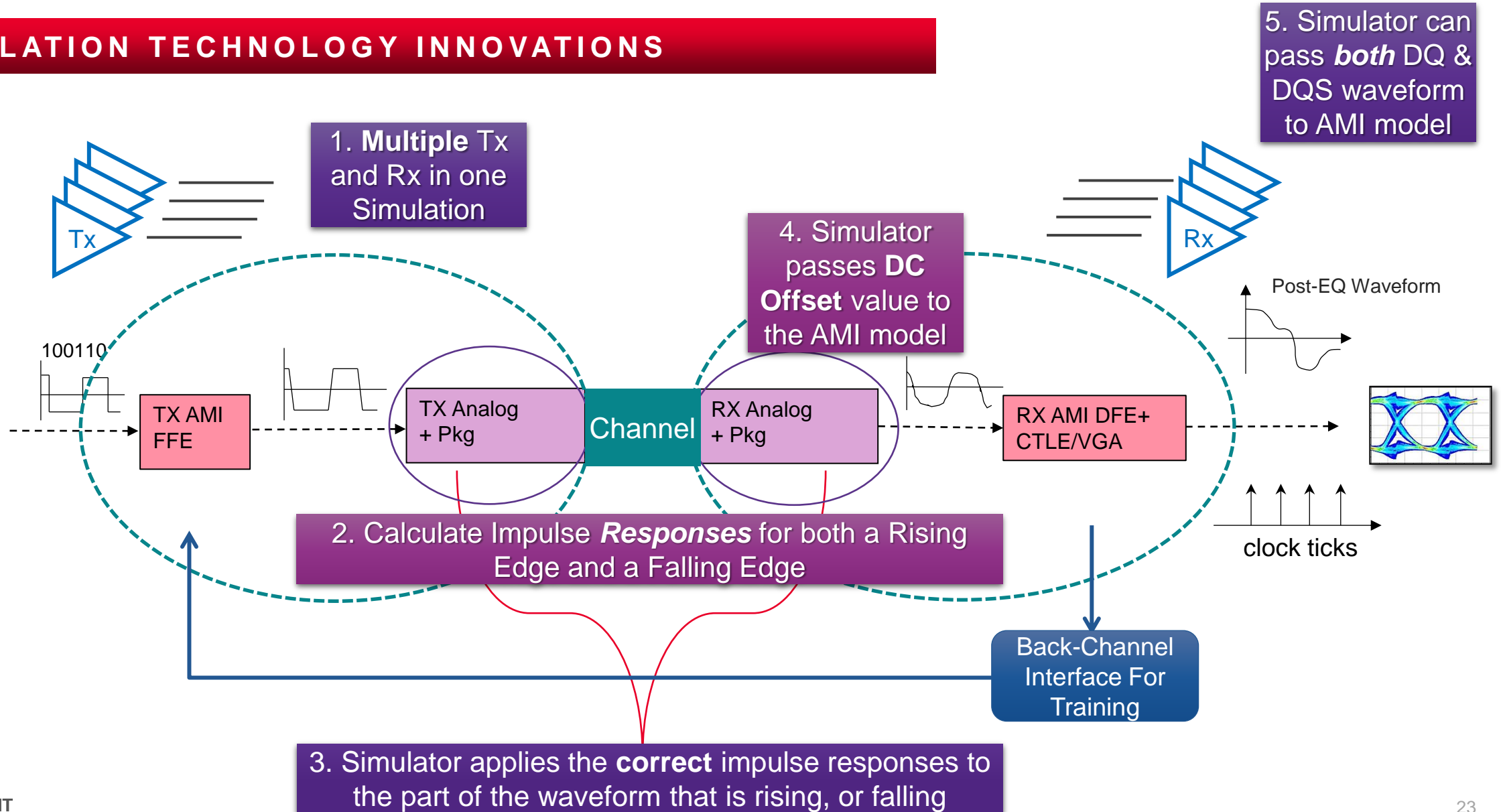
# What Do We Need for DDR5 AMI To Work?

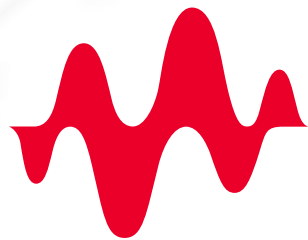
SUPPORTING PARALLEL, SINGLE-ENDED SIGNALS WITH EXTERNAL CLOCKS



# The Solution

## SIMULATION TECHNOLOGY INNOVATIONS





**KEYSIGHT**  
TECHNOLOGIES

4.50221